Thermal stability of SiO₂-coated SiC fiber (Hi-Nicalon) under argon atmosphere

T. SHIMOO, K. OKAMURA

Department of Metallurgy and Materials Science, College of Engineering, Osaka Prefecture University, Sakai, Osaka 599-8531, Japan

F. TOYODA Graduate Student, Osaka Prefecture University, 1-1, Gakuen-cho, Sakai, Osaka 599-8531, Japan E-mail: shimoo@mtl.osakafu-u.ac.jp

Thermal stability of low-oxygen SiC fiber (Hi-Nicalon) coated with SiO₂ film was investigated. The SiO₂ film of same thickness but different crystal structure was formed by heating low-oxygen SiC fiber (Hi-Nicalon) under different oxidation conditions. The oxidation treatment and the subsequent exposure at 1773 K in argon caused very little loss of strength for unoxidized core. For as-oxidized fiber with SiO₂ film which contained imperfections, further loss of strength was caused after exposure in argon. There was little degradation of core strength on being exposed repeatedly at rapid heating and cooling rate in argon. The fiber oxidized at 1773 K kept high level of strength even after exposure at 1823 K. This is because the change in crystal structure of SiO₂ film before and after exposure in argon, which was the controlling factor in the degradation of strength, was diminished with increasing oxidation temperature. © *2000 Kluwer Academic Publishers*

1. Introduction

Polycarbosilane-derived low-oxygen silicon carbide fiber fabricated by electron beam irradiation curing method (Trade name: Hi-Nicalon, Nippon Carbon Co., Tokyo, Japan) has been often utilized as reinforcing material in ceramic matrix composites because of its excellent thermal stability [1, 2]. Hi-Nicalon fiber is composed from β -SiC nanocrystallite, free carbon and a small amount of amorphous silicon oxycarbide (SiC_XO_Y) phase [3, 4]. The SiC_XO_Y phase is thermodynamically unstable at elevated temperatures. Long time of heating above 1673 K causes thermal decomposition of SiC_XO_Y phase, resulting in the gradual degradation of fiber strength. The promising method for improvement of the thermal stability is a suitable covering to restrict the outward transport of decomposed gases, SiO and CO. In particular, SiO₂ film produced by oxidation treatment was very effective in retarding the decomposition reaction of silicon carbide fiber fabricated by oxidation curing method (Trade name: Nicalon, Nippon Carbon Co., Tokyo, Japan) [5, 6]. The formation of SiO₂ film can be less expensively achieved by using a relatively simple equipment. Furthermore, the ceramics produced by hot-pressing pre-oxidized fibers were found to have excellent high-temperature characteristics [7].

The SiO₂-coating developed the thermal stability of Hi-Nicalon fiber as well as that of Nicalon fiber [8]. Consequently, coatings of $0.3-0.4 \mu m$ thick were found to be most effective in suppressing the thermal decomposition of unoxidized core and keeping high levels of

strength. In present work, the SiO₂ films of 0.3–0.4 μ m thick but different crystal structure such as amorphous, nanocrystalline or highly crystallized phase were formed by oxidizing Hi-Nicalon fiber for different oxidation times at 1073–1773 K. Subsequently the oxidized fibers were exposed for at 1773 or 1823 K in argon. In addition, the resistance of SiO₂ film to the exposure repeated at a rapid heating and cooling rate was investigated. The microstructure and strength of both as-oxidized and exposured fibers were determined to evaluate the thermal stability of SiO₂ coated fiber. The oxidation treatment of making most protective SiO₂ film was well established.

2. Experimental procedure

The sample used in this study is the low-oxygen silicon carbide fiber (Hi-Nicalon) manufactured by Nippon Carbon Co. It has molar composition of SiC_{1.40}O_{0.05} and mean diameter of 15 μ m . Fibers were oxidized at temperatures from 1073 to 1773 K in air by using the SiC resistance furnace. The oxidation conditions of fibers and the characterization of as-oxidized fibers are given in Table I. The mass gain due to the oxidation of fiber was measured by an automatic recording balance. The oxidation time was controlled to form the SiO₂ film of 0.3–0.4 μ m thickness. The thickness of SiO₂ film, *b* was calculated from the oxidized fraction of fibers determined by a digital-type automatic recording balance as follow:

TABLE I Oxidation treatment of low-oxygen SiC fiber (Hi-Nicalon)

Oxidation condition			Tensile strength (GPa)	
Temperature (K)	Time (h)	Crystal structure of SiO ₂ film	with SiO ₂	without SiO ₂
1073	200	amorphous	3.04	3.08
1173	150	amorphous	2.79	3.09
1273	100	amorphous	2.57	2.83
1373	50	amorphous	2.33	2.83
1473	30	cristobalite	2.46	2.94
1573	24	cristobalite	2.27	2.79
1673	12	cristobalite	2.11	2.80
1773	5	cristobalite	1.98	2.84

$$b = r_0 \{1 - (1 - X)\}^{1/2}$$
(1)

where r_0 is the radius of fiber and X is the oxidized fraction of fiber.

$$X = \frac{\Delta W}{\Delta W_{100}} \tag{2}$$

 ΔW and ΔW_{100} are the mass gain after oxidation treatment and that after 100% oxidation of fiber, respectively.

The oxidized fibers were subsequently exposed under argon atmosphere as follows: 500 mg of oxidized fibers, 3 cm in length were charged in a magnesia crucible and then was rapidly positioned in the hot zone of furnace controlled at the given temperature. Argon was flowed from the bottom of the furnace at flow rate of 8.33×10^{-6} m³/s. Upon completion of exposure test, the fibers were quenched by raising the crucible to the low temperature zone of the furnace.

The exposure tests of fiber were conducted under three types of heat-treatment condition:

(1) the heat treatment which consists of the heating to 1773 K, the holding of 18 ks and the cooling to room temperature (test A)

(2) the heat treatment which consists of the heating to 1823 K, the holding of 18 ks and the cooling to room temperature (test B)

(3) five times repetition of the heat treatment which consists of the heating to 1773 K, the holding of 3.6 ks and the cooling to room temperature (test C).

Both the oxidized fibers and exposed fibers were characterized in the following way : The crystal structure of fibers was studied by X-ray diffraction, and the morphology of fibers was observed by the scanning electron microscope. The room-temperature tensile strength of a fiber of 10 mm gauge length was determined with a universal tensile testing instrument (Orientec Co., Type TENSILON UTM-II-20, Tokyo, Japan) using a load cell of 100 g and a crosshead speed of 2 mm/min. An average of 20 measurements was tested for each heat-treated fiber. Tensile tests also were conducted for the fibers of which SiO₂ film was removed with NH₄F + HF solution, in order to determine the strength of unoxidized core.

3. Results

Fig. 1 shows the Auger electron spectroscopic measurement of surface concentration for the fiber oxidized for 30 h at 1473 K in air. The oxide layer of about 0.34 μ m thickness is distinctly formed around the fiber. This implies that the oxidized fibers are coated with a smooth and continuous SiO₂ film. The smooth appearance of the oxidized fibers is observed by SEM observation. The SiO₂ film shifts to the unoxidized core via the region having the linear concentration gradients of oxygen and carbon. AES depth profile shows that the value calculated by Equation 1 is found reasonable as the SiO₂ film thickness.

X-ray diffraction patterns are shown in Fig. 2 for fibers oxidized at the oxidation conditions which are given in Table I. The broad pattern at diffraction angle of $2\theta = 22^{\circ}$ reveals that SiO₂ film formed around fibers is amorphous silica below 1373 K. The very week diffraction peak of cristobalite was observed in the fibers oxidized at 1473 and 1573 K, showing that the SiO₂ film is in the nanocrystalline structure. On the other hand, the fibers oxidized at 1673 and 1773 K have the highly crystallized SiO₂ film, owing to the sharp cristobalite peak. Thus, it is found that the crystallization of SiO₂ film develops with increasing the oxidation temperature. In addition, the diffraction pattern of β -SiC becomes sharp



Figure 1 AES depth profile of fiber oxidized for 30 h at 1473 K in air.



Figure 2 X-ray diffraction patterns of fibers oxidized under oxidation conditions shown in Table I.

at 1673 and 1773 K. This means that the thermal decomposition of fiber occurs at the earliest stage of oxidation because of incomplete coating of fiber with SiO_2 film.

The oxidation-treated fibers were exposed for 18 ks at 1773 K in argon (test A). Figs 3 and 4 show the roomtemperature tensile strength for as-oxidized fibers and SiO_2 -removed fibers (unoxidized core) before and after exposure, respectively. As can be seen from Fig. 3, the strength of the as-oxidized fiber with SiO_2 film decreases gradually with increasing oxidation temperature. It clearly shows that the further degradation of fiber strength of as-received (unoxidized) fiber decreases markedly, virtually to zero, the oxidized fiber retains 56-75% of as-received strength. Fig. 4 exhibits that the strength of SiO_2 -removed fiber, that is, unoxidized core, retains almost unchanged in the as-oxidized state in-



Figure 3 Relationship between tensile strength of fibers with SiO_2 film and oxidation temperature.



Figure 4 Relationship between tensile strength of SiO₂-removed fibers and oxidation temperature.

dependently on the oxidation temperature. In addition, there is little the decrease in strength of unoxidized core even after the exposure in argon. Thus, the strength of unoxidized core is kept in the level comparable to asreceived strength of 3.08 GPa. As a result, the strength of the fibers with SiO₂ film is lower than that of SiO₂-removed fiber. This is thought to be because the SiO₂ film often contains imperfections such as pores, voids and flaws.

After exposure of 18 ks at 1773 K in argon, considerable level of strength was retained even in the fiber with SiO_2 film. Therefore, the exposure tests for the SiO_2 -coated fibers were carried out under more severe conditions: the exposure test at 1823 K (test B), and the exposure test in which rapid heating and cooling is repeated five times at temperatures between room-temperature and 1773 K (test C).

Figs 5–7 show the X-ray diffraction patterns of fibers oxidized at 1073, 1473 and 1773 K, respectively. The SiO₂ film formed by the oxidation at 1073 K is amorphous. It crystallizes into cristobalite during continuous exposure of 18 ks at 1773 K (test A) and repeated exposure at 1773 K (test C). After exposure of 18 ks at 1823 K (test B), the SiO₂ film disappears and the unoxidized core crystallizes highly into β -SiC. For the fiber oxidized at 1473 K, the marked crystallization of SiO₂ film is observed after test B. On the other hand,



Figure 5 X-ray diffraction patterns of fibers exposed in argon after oxidaton of 200 h at 1073 K. (A): as-oxidized, (B): continuous exposure of 5 h at 1773 K (test A), (C): continuous exposure of 5 h at 1823 K (test B), (D): repeated exposure of 1 h at 1773 K (test C).



Figure 6 X-ray diffraction patterns of fibers exposed in argon after oxidaton of 30 h at 1473 K. (A): as-oxidized, (B): continuous exposure of 5 h at 1773 K (test A), (C): continuous exposure of 5 h at 1823 K (test B), (D): repeated exposure of 1 h at 1773 K (test C).



Figure 7 X-ray diffraction patterns of fibers exposed in argon after oxidaton of 5 h at 1773 K. (A): as-oxidized, (B): continuous exposure of 5 h at 1773 K (test A), (C): continuous exposure of 5 h at 1823 K (test B), (D): repeated exposure of 1 h at 1773 K (test C).



Figure 8 Relationship between SiO₂ crystallite size and oxidation temperature.

the SiO_2 film of the fiber oxidized at 1773 K is crystalline, and further crystallization is not caused after all the exposure tests.

The crystallite size of SiO₂ was calculated from the half-width value of peak at diffraction angle of $2\theta = 22^{\circ}$ using Scherrer's equation. Fig. 8 shows the crystallite size of SiO₂, D_{SiO_2} for the fibers oxidized at 1073, 1473 and 1773 K. It is can be seen that SiO₂ film has a tendency to crystallize and coarsen during exposure in argon. This tendency is enhanced with decreasing the oxidation-treatment temperature of fiber. In particular, marked coarsening of SiO₂ crystals was observed in the fibers oxidized at 1073 K and subsequently exposed at 1823 K (test B). The value D_{SiO_2} of 56 nm was measured just before the fiber was completely decomposed.

Fig. 9 shows the relationship between the roomtemperature strength of SiO₂-removed fiber (unoxidized fiber) and oxidation temperature. As mentioned earlier, only a slight loss of strength is observed after exposure of 18 ks at 1773 K (test A). After exposure of 18 ks at 1823 K (test B), the strength for the fibers oxidized at 1073 K is completely lost, virtually to zero



Figure 9 Relationship between tensile strength of SiO₂-removed fiber and oxidation temperature.

value, though that for the fibers oxidized at 1473 and 1773 K is kept in high levels. Furthermore, the repeated exposure test (test C) demonstrates that the rapid heating and cooling between room-temperature and 1773 K occurs only a slight degradation of fiber strength. It may be noted that the strengths of the fiber oxidized at 1773 K are nearly identical to that of as-oxidized fiber after exposure tests.

The morphologies of fiber surface are shown in Fig. 10. The SiO₂ films of all as-oxidized fibers have very smooth appearance (photos A and D). The double structure consisting of rough surface and smooth core was observed only for the fiber which was exposed to 1823 K after oxidation treatment at 1073 K (photos B and C). Fiber surface and fractured surface for all the other fibers were smooth and glassy, as well as that for the fiber exposed to 1823 K after oxidation treatment at 1473 K (photos E and F).

4. Discussion

Hi-Nicalon has an excellent thermal stability, owing to small amounts of unstable silicon oxycarbide phase, SiC_XO_Y . The fiber strength remains almost unchanged below 1673 K in argon. The degradation of strength is gradual at 1673 to 1873 K and then is serious above 1873 K [4, 5]. As can be seen from Fig. 2, the strength of unoxidized core (SiO₂-removed fiber) was reduced by about 10% even after oxidation of 18 ks at 1273 K. This degradation of strength is not due to the thermal decomposition of SiC_XO_Y phase which occurs above 1473 K [4, 5]. Hi-Nicalon fiber also contains SiC nanocrystals and the intergranular free carbon phase. The free carbon phase forms a continuous framework between the SiC nanocrystals [4]. The unoxidized core is oxidized by the inward diffusion of oxygen molecules through SiO₂ film [9, 10]. Therefore, microimperfections are probably formed on the surface of unoxidized core by the preferential oxidation of the free carbon



Figure 10 Morphology of fiber surface. photo A: as-oxidized at 1073 K, photos B and C: exposed at 1823 K after oxidation at 1073 K, photo D: as-oxidized at 1473 K, photos E and F: exposed at 1823 K after oxidation at 1473 K.

phase, resulting in a slight reduction of strength. If the oxidation temperature exceeds the decomposition temperature of amorphous SiC_XO_Y phase (about 1473 K), the liberation of decomposed gases, i.e. SiO and CO, and the crystallization into SiC occur at earliest stage of oxidation because of imperfectly coating with SiO₂ film. This is substantiated by X-ray diffraction result (Fig. 2). The formation of protective SiO₂ film seems to suppress further decomposition of unoxidized core by restricting the outward diffusion of both SiO and CO gases. Therefore, the thermal decomposition occurs only slightly in an oxidizing gas such as air.

From comparison of Fig. 2 with Fig. 3, the strengthcontrolling imperfections are thought to be principally contained in SiO₂ fillm. In addition, the strength of as-oxidized fiber with SiO₂ film, as a consequence of the crystallization of SiO₂ film and coarsening of SiO₂ grains, decreases with increasing oxidation temperature. X-ray diffraction reveals that the exposure of oxidized fibers in argon has a tendency to cause further the crystallization of SiO₂ film and the coarsening of SiO₂ grains. Since new imperfections such as pores, voids and cracks are produced in SiO₂ film, further degradation of fiber strength occurs during continuous exposure of 18 ks at 1773 K in argon (test A). The degradation of strength is more severe for the fiber oxidized at lower temperatures. As can be seen from Fig. 8, this is attributable to not the SiO₂ grain size after exposure, but the magnitude of increase in SiO₂ grain size during exposure. In particular, marked increase in SiO₂ grain size, as well as the crystallization of amorphous silica into to cristobalite, was observed for the fiber oxidized at 1073 K. As mentioned above, a considerable degradation of strength is to be avoided for the as-oxidized fibers with SiO_2 film, owing to the formation of imperfections in SiO_2 film. On the other hand, the strength of unoxidized cores is little lost during oxidation treatment and continuous exposure at 1773 K (test A).

As shown in Fig. 9, the unoxidized core (SiO₂removed fiber) also deteriorates for the fibers exposed under severe conditions. While the continuous exposure of 18 ks at 1823K (test B) causes a slight degradation of the strength for the fibers oxidized at 1473 and 1773 K, test B causes marked degradation of the strength for the fiber oxidized at 1073 K, practically to 0 Gpa. The SiO₂ grains coarsen markedly after exposure at 1823 K: the increase in grain size from 0.6 to 56 nm, resulting in the production of serious imperfections in SiO₂ film. Since the SiO₂ film is proof no longer against the decomposition pressure of unoxidized core (i.e. the pressures of SiO and CO) at 1823 K, the disappearance of SiO₂ film and the resultant decomposition of unoxidized core occur. The center of the fiber has a smooth and glassy fracture surface (Fig. 10, photo C), showing that thermal decomposition is retarded in this region. However, the fiber strength is nearly perfectly lost. This seems to be because the cracks from coarsened surface propagate to the center.

From Fig. 10, it can be seen that the SiO_2 grain size after repeated exposure test (test C) is nearly identical to that after continuous exposure test (test A). However, test C causes greater loss of strength than test A, particularly for the fiber oxidized at low temperature of 1073 K. Therefore, the repeated exposure, that is, a rapid repetition of heating and cooling produce the imperfections in unoxidized core as well as in SiO_2 film.

Finally, the fiber oxidized at 1773 K has the most excellent thermal stability, owing to the small change in crystal structure of SiO_2 film before and after all exposure tests.

5. Conclusions

Low-oxygen silicon carbide fiber (Hi-Nicalon) was coated with the SiO₂ film with different crystal structure of 0.3–0.4 μ m thickness by oxidizing for different times at 1073–1773 K in air. Subsequently, the fiber was heated in argon under three type of exposure condition: continuous exposure of 18 ks at 1773 K (test A), continuous exposure of 18 ks at 1823 K (test B) and five times-repeated exposure of 3.6 ks at 1773 K (test C).

The strength of SiO₂-removed fiber (unoxidized core) retained 91–100% of as-received strength after oxidation treatment. There was little degradation of strength after test A. On the other hand, the strength of as-oxidized fiber with SiO₂ film decreased significantly with increasing oxidation temperature, and it decreased further after test A. This tendency was enhanced after test B. Test B caused large change in the crystal structure of SiO₂ film for the fiber oxidized at 1073 K, resulting in the disappearance of SiO₂ film and the degradation of fiber strength to 0 GPa. All the SiO₂ film were proof of test C, although there was a considerable reduction of strength for the fiber oxidized at low temperature. The change in the crystal structure

of SiO₂ film is thought to be the controlling factor in the degradation of fiber strength. Since the highly crystallized SiO₂ film remained almost unchanged during exposure, the fiber oxidized at 1773 K was retained a high level of strength after all the exposure tests.

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